

**SDR950E
thru
SDR952E**

Designer's Data Sheet

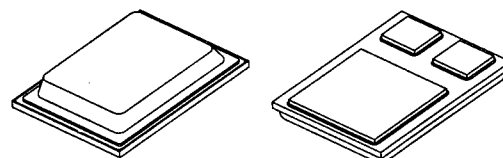
FEATURES:

- Hyper Fast Recovery: 35 nsec Maximum
- High Surge Rating
- Low Reverse Leakage Current
- Low Junction Capacitance
- Hermetically Sealed Surface Mount Package
- Gold Eutectic Die Attach available
- Ultrasonic Aluminum Wire Bonds

- TX, TXV and Space Level Screening Available

**60 AMP
100-200 VOLTS
35 nsec
HYPER FAST
RECTIFIER**

MILPACK™ 1



MAXIMUM RATINGS

RATING	SYMBOL	VALUE	UNIT
Peak Repetitive Reverse and DC Blocking Voltage SDR950E SDR951E SDR952E	VRRM VRWM VR	 100 150 200	 Volts
Average Rectified Forward Current (Resistive Load, 60Hz, Sine Wave, TA=25°C)	Io	60	Amps
Peak Surge Current (8.3 ms Pulse, Half Sine Wave, TA=25°C) note 1	IFSM	600	Amps
Operating and storage temperature	Top & Tstg	-65 to +200	°C
Maximum Thermal Resistance Junction to Case	RθJC	0.8	°C/W

note 1 Connect pins 2 & 3 together

NOTE: All specifications are subject to change without notification.
SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET#: RH0227B

SDR950E thru SDR952E

PRELIMINARY

SSDI
SOLID STATE DEVICES, INC

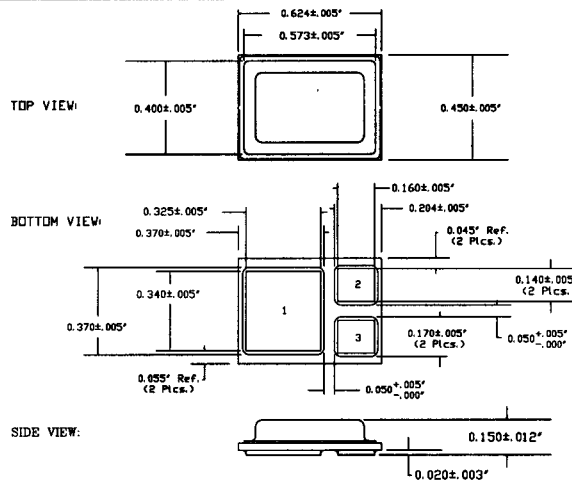
14849 Firestone Boulevard · La Mirada, CA 90638
Phone: (714) 670-SSDI (7734) · Fax: (714) 522-7424

ELECTRICAL CHARACTERISTICS

CHARACTERISTICS	SYMBOL	MAXIMUM	UNIT
Instantaneous Forward Voltage Drop (IF = 25 Adc, TA=25°C, 300μs Pulse) (IF = 50 Adc, TA=25°C, 300μs Pulse)	VF	0.95 1.05	Vdc
Instantaneous Forward Voltage Drop (IF = 50 Adc, TA= 100°C, 300μs Pulse) (IF = 25 Adc, TA= - 55°C, 300μs Pulse)	VF	0.85 1.20	Vdc
Reverse Leakage Current (Rated VR, TA=25°C, 300μs pulse minimum)	IR	100	μA
Reverse Leakage Current (Rated VR, TA=100°C, 300μs pulse minimum)	IR	10	mA
Junction Capacitance (VR = 10 Vdc, TA=25°C, f= 1 MHz)	CJ	450	pf
Reverse Recovery Time (IF=500mA, IR=1 A, IRR=250mA, TA=25°C)	t_{rr}	35	nsec

CASE OUTLINE: MILPACK

PIN 1: CATHODE
PIN 2: ANODE
PIN 3: ANODE



Note: Tolerances are ±.005" unless otherwise specified.

TYPICAL OPERATING CURVES TA=25°C Unless otherwise specified

